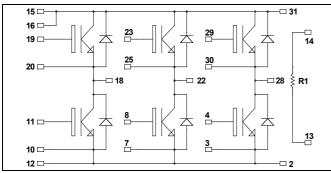
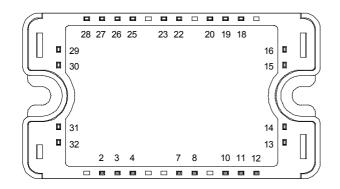


## 3 Phase bridge Trench + Field Stop IGBT3 Power Module



It is recommended to connect a decoupling capacitor between pins 31 & 2 to reduce switching overvoltages, if DC Power is connected between pins 15, 16 & 12. Pins 15 & 16 must be shorted together.



## $V_{CES} = 600V$ $I_{C} = 30A$ @ Tc = 80°C

#### **Application**

Motor control

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	50	
$I_{C}$	Continuous Conector Current	$T_C = 80$ °C	30	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	60	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	90	W
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150$ °C	60A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $T_j = 25^{\circ}C$			1.5	1.9	V
$V_{CE(sat)}$		$I_C = 30A$ $T_j = 15$	$T_{j} = 150^{\circ}C$		1.7		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400 \mu A$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				300	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			1600		
Coes	Output Capacitance				110		pF
C <sub>res</sub>	Reverse Transfer Capacitance				50		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switchi	ing (25°C)		110		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			45		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 30A$			200		
$T_{\rm f}$	Fall Time	$R_G = 10\Omega$			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switchi	ing (150°C)		120		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			50		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_C = 30A$		250		113	
$T_{\rm f}$	Fall Time	$R_G = 10\Omega$			60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.16		mJ
Lon	Turn-on Switching Energy	$V_{Bus} = 300V$	$T_{j} = 150^{\circ}C$		0.3		1113
$E_{off}$	Turn-off Switching Energy	$ \begin{array}{c} I_C = 30A \\ R_G = 10\Omega \end{array} \qquad \begin{array}{c} T_j = 25^{\circ}C \\ T_j = 150^{\circ}C \end{array} $	$T_j = 25^{\circ}C$		0.7		mJ
Loff				1.05		1113	

### Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Test Conditions		Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_j = 25$ °C			250	μΑ
1KM		V R 000 V	$T_{j} = 150^{\circ}C$			500	μ1
$I_{\mathrm{F}}$	DC Forward Current		Tc = 80°C		30		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 30A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
<b>▼</b> F	Diode Forward Voluge		$T_i = 150$ °C		1.5		•
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25$ °C		100		ns
CIT	reverse recovery Time		$T_j = 150$ °C		150		113
$Q_{rr}$	Reverse Recovery Charge $ \begin{aligned} I_F &= 30A \\ V_R &= 300V \\ di/dt &= 1800A/\mu s \end{aligned} $	$I_F = 30A$ $V_P = 300V$	$T_j = 25$ °C		1.5		μC
Qrr		$T_{j} = 150^{\circ}C$		3.1		μС	
Е	E <sub>r</sub> Reverse Recovery Energy		$T_j = 25^{\circ}C$		0.34		mJ
$\mathbf{L}_{\mathrm{f}}$			$T_j = 150$ °C		0.75		1113

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Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

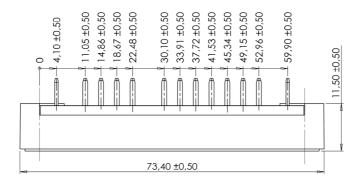
$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{75}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

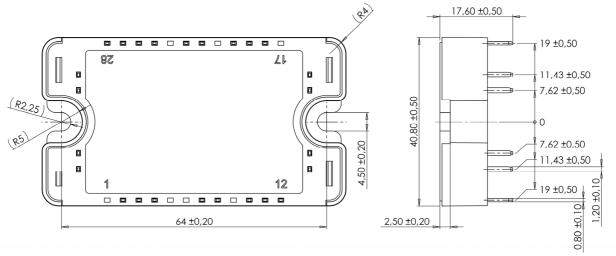
$$R_{T}: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{\text{thJC}}$	Junction to Case Thermal Resistance		IGBT			1.6	°C/W
	Junction to Case Thermal Resistance	Diode			2.45	C/ VV	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		175		
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

### SP3 Package outline (dimensions in mm)





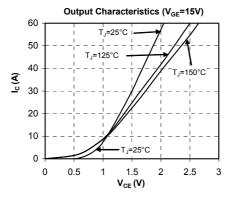
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

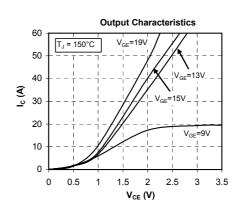
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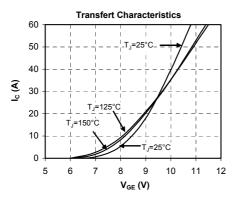
3 - 6

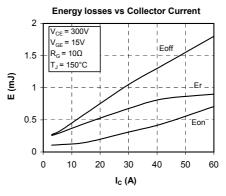


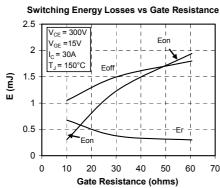
### **Typical Performance Curve**

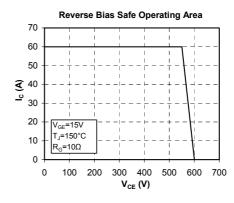


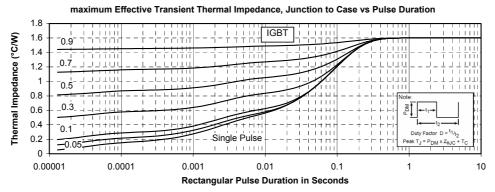






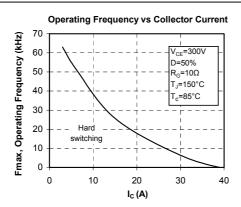


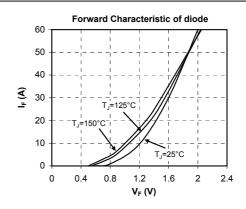


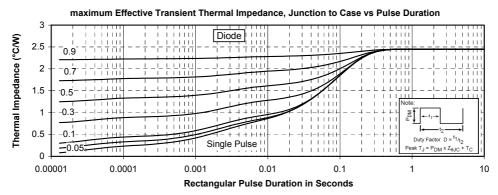


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